

**5 V, SUPER MINIMOLD SILICON MMIC
MEDIUM OUTPUT POWER AMPLIFIER**

DESCRIPTION

The μPC2710TB is a silicon monolithic integrated circuit designed as PA driver for 900 MHz band cellular telephone tuners. This IC is packaged in super minimold package which is smaller than conventional minimold.

This IC is manufactured using NEC's 20 GHz fr NESAT™ III silicon bipolar process. This process uses silicon nitride passivation film and gold electrodes. These materials can protect chip surface from external pollution and prevent corrosion/migration. Thus, this IC has excellent performance, uniformity and reliability.

FEATURES

- Supply voltage : $V_{CC} = 4.5$ to 5.5 V
- Circuit current : $I_{CC} = 22$ mA TYP. @ $V_{CC} = 5.0$ V
- Power gain : $G_P = 33$ dB TYP. @ $f = 500$ MHz
- Medium output power : $P_{O(sat)} = +13.5$ dBm TYP. @ $f = 500$ MHz
- Upper limit operating frequency : $f_u = 1.0$ GHz TYP. @ 3 dB bandwidth
- Port impedance : input/output 50Ω
- High-density surface mounting : 6-pin super minimold package ($2.0 \times 1.25 \times 0.9$ mm)

APPLICATION

- PA driver for 900 MHz band cellular telephone

ORDERING INFORMATION

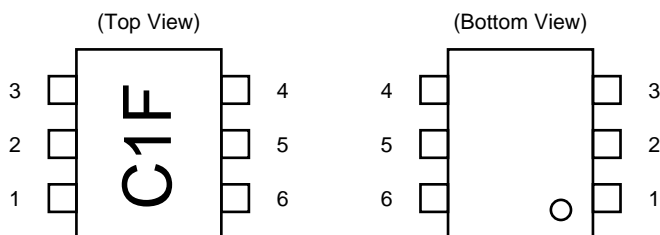
Part Number	Package	Marking	Supplying Form
μPC2710TB-E3	6-pin super minimold	C1F	Embossed tape 8 mm wide. 1, 2, 3 pins face the perforation side of the tape. Qty 3 kpcs/reel.

Remark To order evaluation samples, please contact your local NEC sales office.
(Part number for sample order: μPC2710TB)

Caution Electro-static sensitive devices

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Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.

PIN CONNECTIONS



Pin No.	Pin Name
1	INPUT
2	GND
3	GND
4	OUTPUT
5	GND
6	V _{CC}

★ **PRODUCT LINE-UP** (T_A = +25°C, V_{CC} = V_{out} = 5.0 V, Z_s = Z_L = 50 Ω)

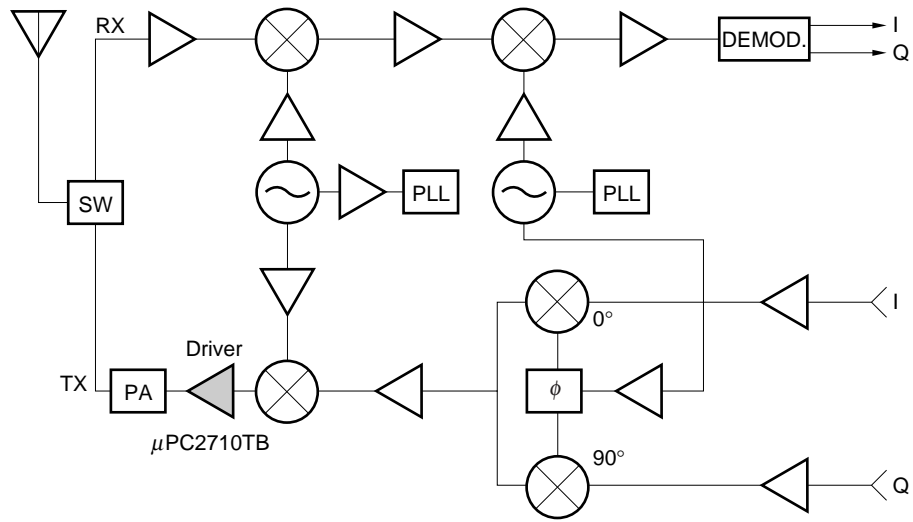
Part No.	f _u (GHz)	P _{O(sat)} (dBm)	G _P (dB)	NF (dB)	I _{CC} (mA)	Package	Marking
μPC2708T	2.9	+10.0	15	6.5	26	6-pin minimold	C1D
μPC2708TB						6-pin super minimold	
μPC2709T	2.3	+11.5	23	5.0	25	6-pin minimold	C1E
μPC2709TB						6-pin super minimold	
μPC2710T	1.0	+13.5	33	3.5	22	6-pin minimold	C1F
μPC2710TB						6-pin super minimold	
μPC2776T	2.7	+8.5	23	6.0	25	6-pin minimold	C2L
μPC2776TB						6-pin super minimold	

Remark Typical performance. Please refer to **ELECTRICAL CHARACTERISTICS** in detail.

Notice The package size distinguishes between minimold and super minimold.

SYSTEM APPLICATION EXAMPLE

EXAMPLE OF 900 MHz BAND DIGITAL CELLULER TELEPHONE



PIN EXPLANATION

Pin No.	Pin Name	Applied Voltage (V)	Pin Voltage (V) <small>Note</small>	Function and Applications	Internal Equivalent Circuit
1	INPUT	–	0.90	Signal input pin. A internal matching circuit, configured with resistors, enables 50 Ω connection over a wide band. A multi-feedback circuit is designed to cancel the deviations of h_{FE} and resistance. This pin must be coupled to signal source with capacitor for DC cut.	
2 3 5	GND	0	–	Ground pin. This pin should be connected to system ground with minimum inductance. Ground pattern on the board should be formed as wide as possible. All the ground pins must be connected together with wide ground pattern to decrease impedance difference.	
4	OUTPUT	Voltage as same as V_{CC} through external inductor	–	Signal output pin. The inductor must be attached between V_{CC} and output pins to supply current to the internal output transistors.	
6	V_{CC}	4.5 to 5.5	–	Power supply pin, which biases the internal input transistor. This pin should be externally equipped with bypass capacitor to minimize its impedance.	

Note Pin voltage is measured at $V_{CC} = 5.0\text{ V}$

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Conditions	Ratings	Unit
Supply Voltage	V _{CC}	T _A = +25°C, pin 4 and pin 6	5.8	V
Total Circuit Current	I _{CC}	T _A = +25°C	60	mA
Power Dissipation	P _D	Mounted on double-sided copper clad 50 × 50 × 1.6 mm epoxy glass PWB T _A = +85°C	270	mW
Operating Ambient Temperature	T _A		-40 to +85	°C
Storage Temperature	T _{stg}		-55 to +150	°C
Input Power	P _{in}	T _A = +25°C	+10	dBm

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RECOMMENDED OPERATING RANGE

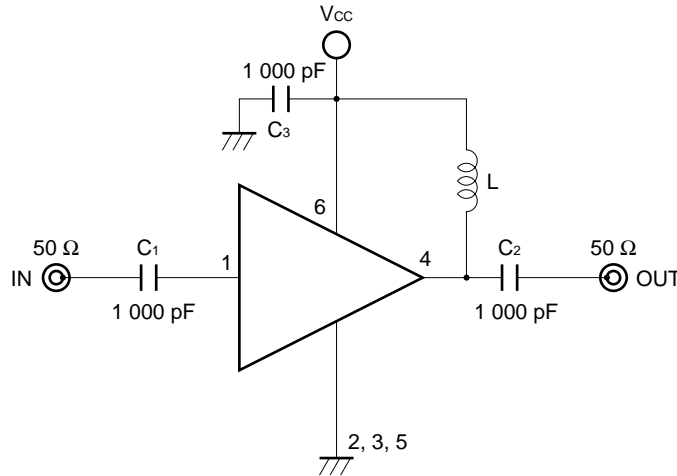
Parameter	Symbol	MIN.	TYP.	MAX.	Unit	Remark
Supply Voltage	V _{CC}	4.5	5.0	5.5	V	The same voltage should be applied to pin 4 and pin 6.

ELECTRICAL CHARACTERISTICS

(Unless otherwise specified, T_A = +25°C, V_{CC} = V_{out} = 5.0 V, Z_s = Z_L = 50 Ω)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Circuit Current	I _{CC}	No signal	16	22	29	mA
Power Gain	G _P	f = 500 MHz	30	33	36.5	dB
Saturated Output Power	P _{O(sat)}	f = 500 MHz, P _{in} = -8 dBm	+11.0	+13.5	-	dBm
Noise Figure	NF	f = 500 MHz	-	3.5	5.0	dB
Upper Limit Operating Frequency	f _u	3 dB down below flat gain at f = 0.1 GHz	0.7	1.0	-	GHz
Isolation	ISL	f = 500 MHz	34	39	-	dB
Input Return Loss	RL _{in}	f = 500 MHz	3	6	-	dB
Output Return Loss	RL _{out}	f = 500 MHz	9	12	-	dB
Gain Flatness	ΔG _P	f = 0.1 to 0.6 GHz	-	±0.8	-	dB

TEST CIRCUIT



COMPONENTS OF TEST CIRCUIT FOR MEASURING ELECTRICAL CHARACTERISTICS

	Type	Value
C ₁ , C ₂	Bias Tee	1 000 pF
C ₃	Capacitor	1 000 pF
L	Bias Tee	1 000 nH

EXAMPLE OF ACTUAL APPLICATION COMPONENTS

	Type	Value	Operating Frequency
C ₁ to C ₃	Chip Capacitor	1 000 pF	100 MHz or higher
L	Chip Inductor	300 nH	10 MHz or higher
		100 nH	100 MHz or higher
		10 nH	1.0 GHz or higher

INDUCTOR FOR THE OUTPUT PIN

The internal output transistor of this IC consumes 20 mA, to output medium power. To supply current for output transistor, connect an inductor between the Vcc pin (pin 6) and output pin (pin 4). Select large value inductance, as listed above.

The inductor has both DC and AC effects. In terms of DC, the inductor biases the output transistor with minimum voltage drop to output enable high level. In terms of AC, the inductor make output-port impedance higher to get enough gain. In this case, large inductance and Q is suitable.

CAPACITORS FOR THE Vcc, INPUT AND OUTPUT PINS

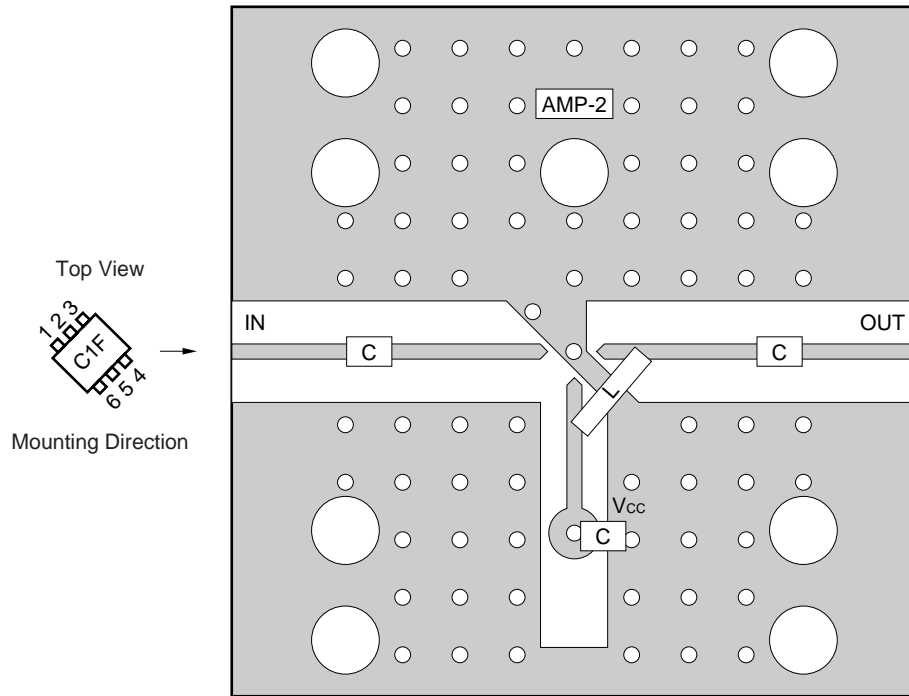
Capacitors of 1000 pF are recommendable as the bypass capacitor for the Vcc pin and the coupling capacitors for the input and output pins.

The bypass capacitor connected to the Vcc pin is used to minimize ground impedance of Vcc pin. So, stable bias can be supplied against Vcc fluctuation.

The coupling capacitors, connected to the input and output pins, are used to cut the DC and minimize RF serial impedance. Their capacitance are therefore selected as lower impedance against a 50 Ω load. The capacitors thus perform as high pass filters, suppressing low frequencies to DC.

To obtain a flat gain from 100 MHz upwards, 1000 pF capacitors are used in the test circuit. In the case of under 10 MHz operation, increase the value of coupling capacitor such as 10000 pF. Because the coupling capacitors are determined by equation, $C = 1/(2 \pi Rf_c)$.

ILLUSTRATION OF THE TEST CIRCUIT ASSEMBLED ON EVALUATION BOARD



COMPONENT LIST

	Value
C	1 000 pF
L	300 nH

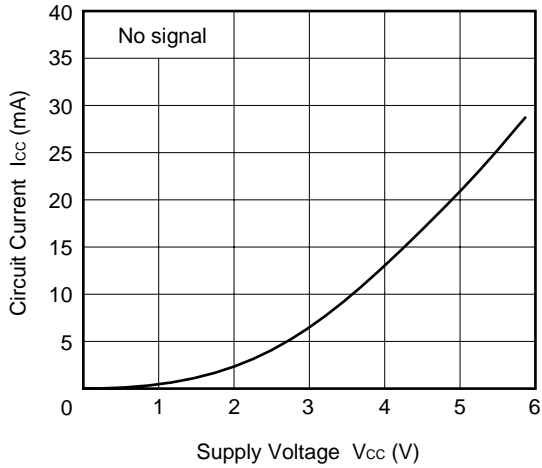
Notes

1. 30 × 30 × 0.4 mm double sided copper clad polyimide board.
2. Back side: GND pattern
3. Solder plated on pattern
4. ○ ○ : Through holes

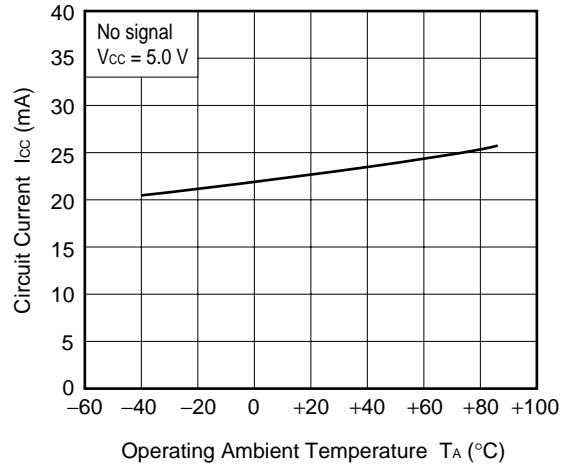
For more information on the use of this IC, refer to the following application note: **USAGE AND APPLICATION OF 6-PIN SUPER MINIMOLD SILICON MEDIUM-POWER HIGH-FREQUENCY AMPLIFIER MMIC (P13252E).**

TYPICAL CHARACTERISTICS (Unless otherwise specified, $T_A = +25^\circ\text{C}$)

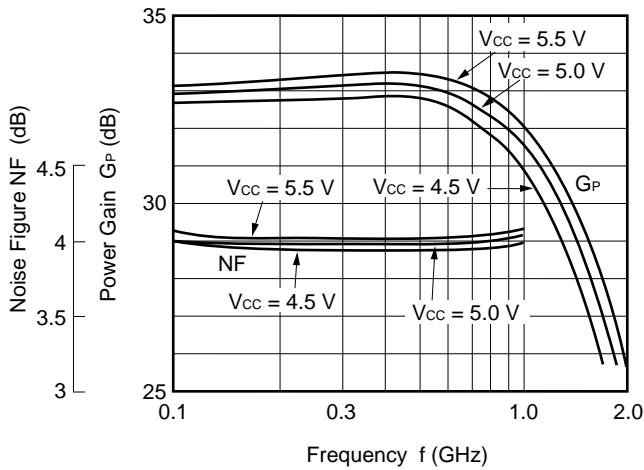
CIRCUIT CURRENT vs. SUPPLY VOLTAGE



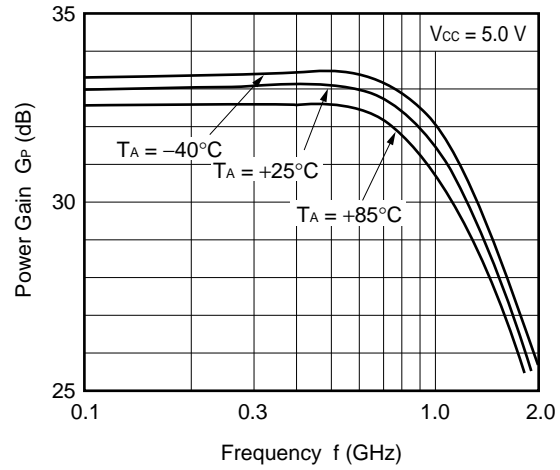
CIRCUIT CURRENT vs. OPERATING AMBIENT TEMPERATURE



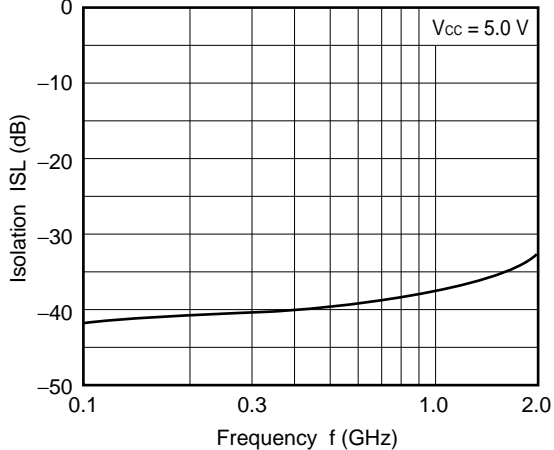
NOISE FIGURE, POWER GAIN vs. FREQUENCY



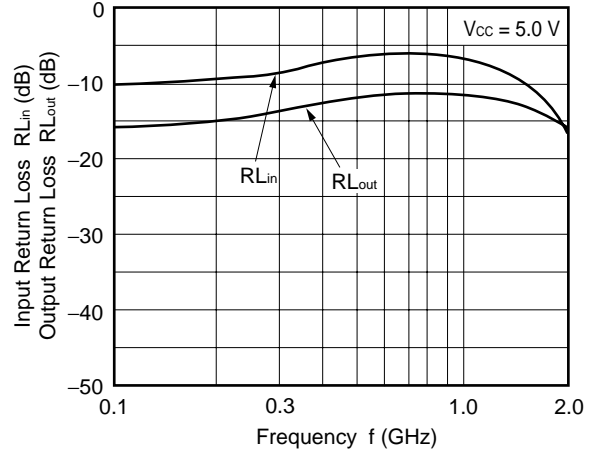
POWER GAIN vs. FREQUENCY



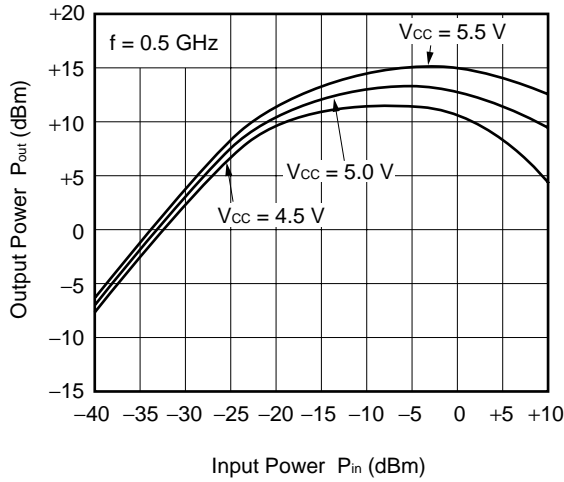
ISOLATION vs. FREQUENCY



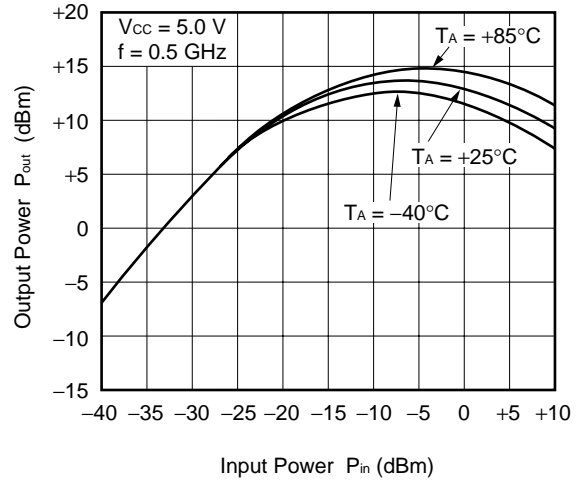
INPUT RETURN LOSS, OUTPUT RETURN LOSS vs. FREQUENCY



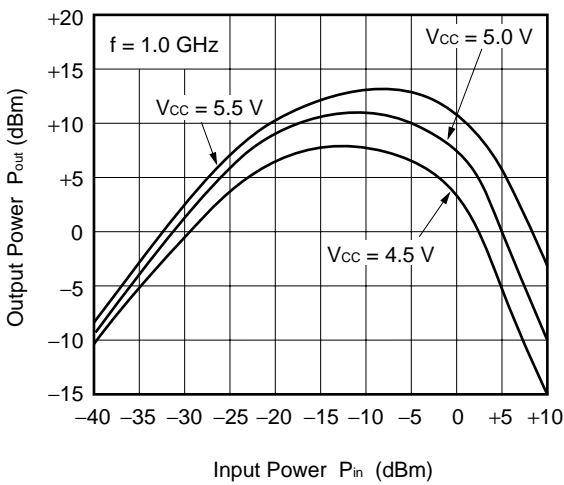
OUTPUT POWER vs. INPUT POWER



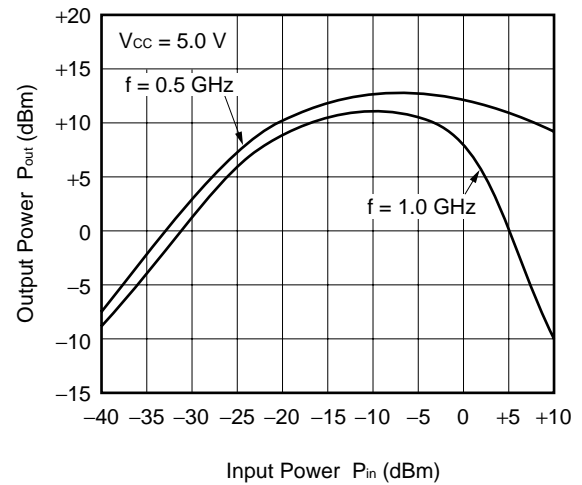
OUTPUT POWER vs. INPUT POWER



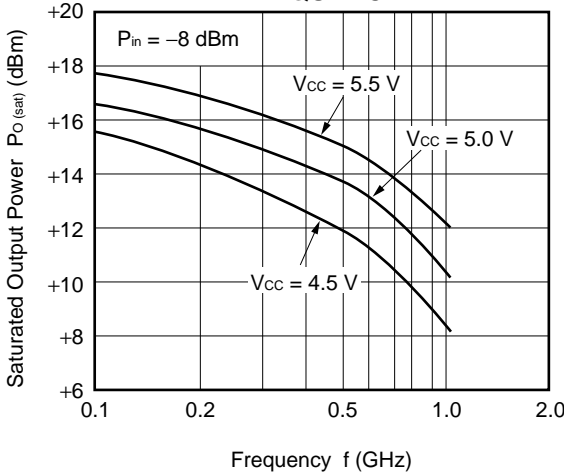
OUTPUT POWER vs. INPUT POWER



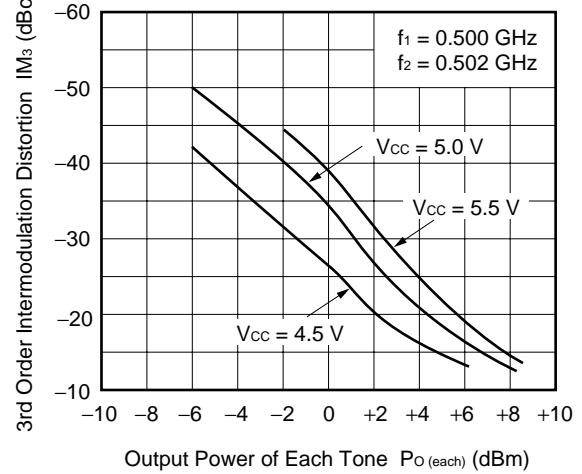
OUTPUT POWER vs. INPUT POWER



SATURATED OUTPUT POWER vs. FREQUENCY

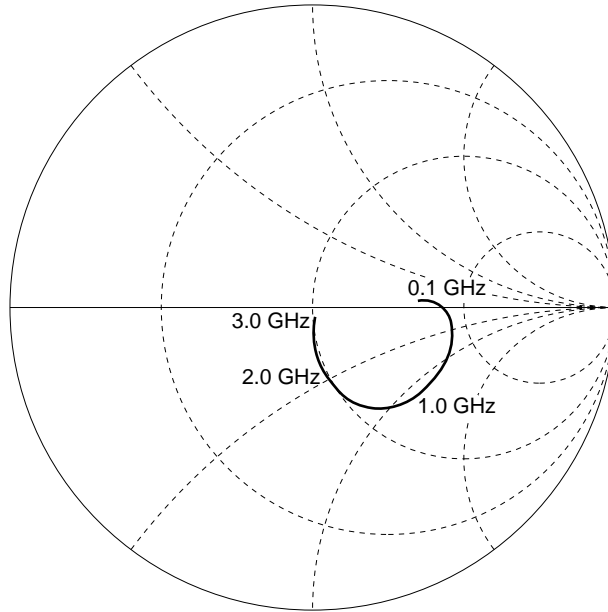


3RD ORDER INTERMODULATION DISTORTION vs. OUTPUT POWER OF EACH TONE

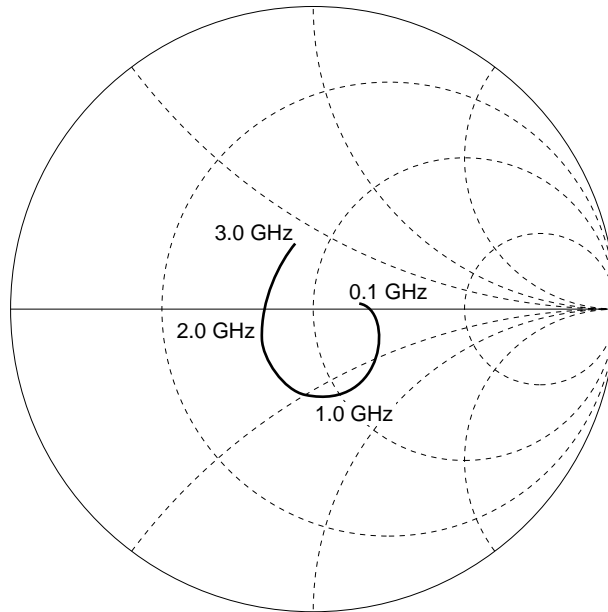


S-PARAMETERS ($T_A = +25^\circ\text{C}$, $V_{CC} = V_{out} = 5.0\text{ V}$)

S₁₁-FREQUENCY



S₂₂- FREQUENCY



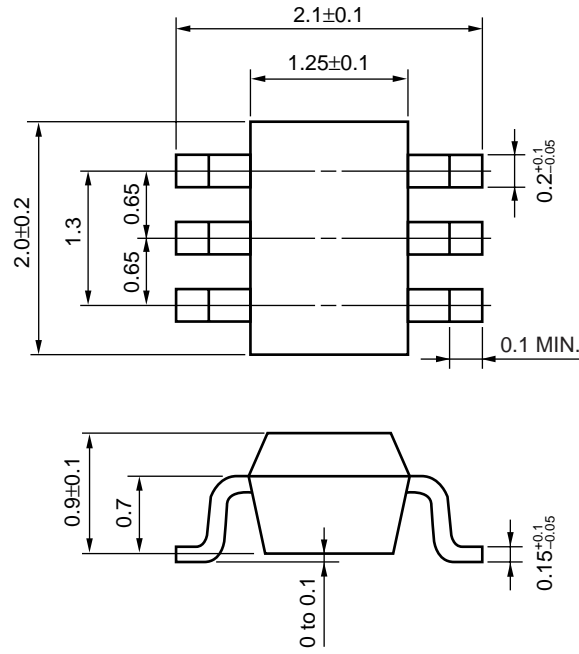
TYPICAL S-PARAMETER VALUES (T_A = +25°C)

V_{CC} = V_{out} = 5.0 V, I_{CC} = 22 mA

FREQUENCY MHz	S ₁₁		S ₂₁		S ₁₂		S ₂₂		K
	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.	
100.0000	0.306	2.5	43.072	-8.4	0.012	15.2	0.156	2.7	1.08
200.0000	0.324	5.2	43.517	-17.1	0.010	10.7	0.164	2.1	1.17
300.0000	0.356	5.3	44.432	-26.5	0.010	20.2	0.185	0.3	1.10
400.0000	0.400	2.5	45.513	-36.9	0.012	26.9	0.225	-5.5	0.92
500.0000	0.439	-3.3	45.679	-48.1	0.012	27.0	0.255	-15.4	0.85
600.0000	0.469	-10.2	45.670	-59.7	0.013	31.3	0.283	-27.6	0.77
700.0000	0.481	-17.9	44.793	-71.8	0.014	34.9	0.301	-40.2	0.74
800.0000	0.488	-26.7	43.016	-84.3	0.014	27.9	0.312	-54.9	0.74
900.0000	0.479	-34.5	40.519	-96.0	0.013	26.6	0.316	-67.7	0.78
1000.0000	0.465	-41.2	37.946	-107.3	0.016	30.8	0.311	-79.5	0.79
1100.0000	0.448	-49.3	35.122	-117.9	0.016	26.6	0.307	-92.2	0.85
1200.0000	0.417	-54.9	32.108	-128.0	0.015	39.5	0.282	-104.6	0.99
1300.0000	0.387	-61.2	29.221	-137.0	0.015	39.7	0.270	-115.5	1.12
1400.0000	0.350	-65.2	26.656	-145.8	0.015	50.2	0.248	-127.0	1.27
1500.0000	0.316	-70.8	23.895	-153.9	0.013	50.8	0.236	-136.2	1.56
1600.0000	0.292	-74.0	21.576	-161.6	0.016	56.6	0.215	-145.3	1.49
1700.0000	0.256	-76.9	19.567	-168.1	0.015	69.0	0.200	-155.2	1.71
1800.0000	0.245	-80.5	17.743	-174.4	0.018	61.7	0.196	-162.5	1.59
1900.0000	0.215	-82.9	16.040	179.6	0.017	70.0	0.180	-173.4	1.88
2000.0000	0.201	-85.6	14.717	173.5	0.021	71.2	0.175	-178.1	1.71
2100.0000	0.177	-84.4	13.475	168.8	0.020	83.0	0.166	172.0	1.94
2200.0000	0.161	-88.8	12.327	163.1	0.021	76.7	0.171	167.7	1.99
2300.0000	0.145	-88.7	11.154	158.7	0.022	87.9	0.159	159.1	2.08
2400.0000	0.124	-90.3	10.262	154.4	0.023	81.4	0.164	154.0	2.15
2500.0000	0.113	-89.8	9.490	150.4	0.025	91.9	0.158	147.0	2.19
2600.0000	0.107	-91.9	8.793	146.4	0.028	88.7	0.166	141.8	2.06
2700.0000	0.091	-92.2	8.149	142.4	0.030	93.4	0.175	135.7	2.13
2800.0000	0.081	-94.9	7.652	138.9	0.031	92.1	0.183	131.6	2.13
2900.0000	0.067	-97.4	7.134	135.1	0.031	93.0	0.191	123.4	2.26
3000.0000	0.055	-103.8	6.726	131.5	0.039	88.3	0.200	118.9	1.97
3100.0000	0.039	-95.6	6.295	128.4	0.039	89.6	0.203	111.5	2.08

★ PACKAGE DIMENSIONS

6-PIN SUPER MINIMOLD (UNIT: mm)



NOTES ON CORRECT USE

- (1) Observe precautions for handling because of electro-static sensitive devices.
- (2) Form a ground pattern as widely as possible to minimize ground impedance (to prevent undesired oscillation).
All the ground pins must be connected together with wide ground pattern to decrease impedance difference.
- (3) The bypass capacitor should be attached to Vcc line.
- (4) The inductor must be attached between Vcc and output pins. The inductance value should be determined in accordance with desired frequency.
- (5) The DC cut capacitor must be attached to input pin and output pin.

RECOMMENDED SOLDERING CONDITIONS

This product should be soldered under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your NEC sales representative.

Soldering Method	Soldering Conditions	Recommended Condition Symbol
Infrared Reflow	Package peak temperature: 235°C or below Time: 30 seconds or less (at 210°C) Count: 3, Exposure limit: None ^{Note}	IR35-00-3
VPS	Package peak temperature: 215°C or below Time: 40 seconds or less (at 200°C) Count: 3, Exposure limit: None ^{Note}	VP15-00-3
Wave Soldering	Soldering bath temperature: 260°C or below Time: 10 seconds or less Count: 1, Exposure limit: None ^{Note}	WS60-00-1
Partial Heating	Pin temperature: 300°C or below Time: 3 seconds or less (per side of device) Exposure limit: None ^{Note}	—

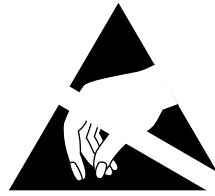
Note After opening the dry pack, keep it in a place below 25°C and 65% RH for the allowable storage period.

Caution Do not use different soldering methods together (except for partial heating).

For details of recommended soldering conditions for surface mounting, refer to information document SEMICONDUCTOR DEVICE MOUNTING TECHNOLOGY MANUAL (C10535E).

[MEMO]

[MEMO]



ATTENTION

OBSERVE PRECAUTIONS
FOR HANDLING
ELECTROSTATIC
SENSITIVE
DEVICES

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